

/ Descriptions

TO-220FL N MOS N-CHANNEL MOSFET in a TO-220FL Plastic Package.

/ Features

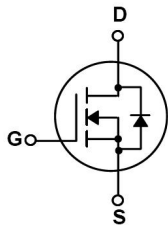
Low gate charge, Low Crss , Fast switching.

/ Applications

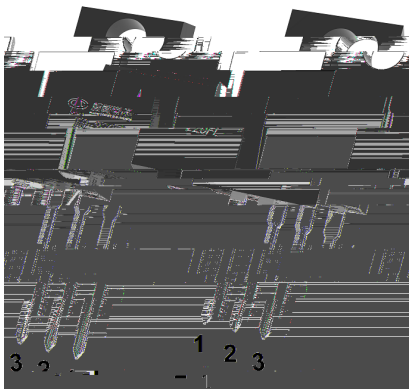
UPS

High efficiency switch mode power supplies, Electronic lamp ballasts based on half bridge, UPS .

/ Equivalent Circuit



/ Pinning



PIN1 G

PIN 2 D

PIN 3 S

/ Marking

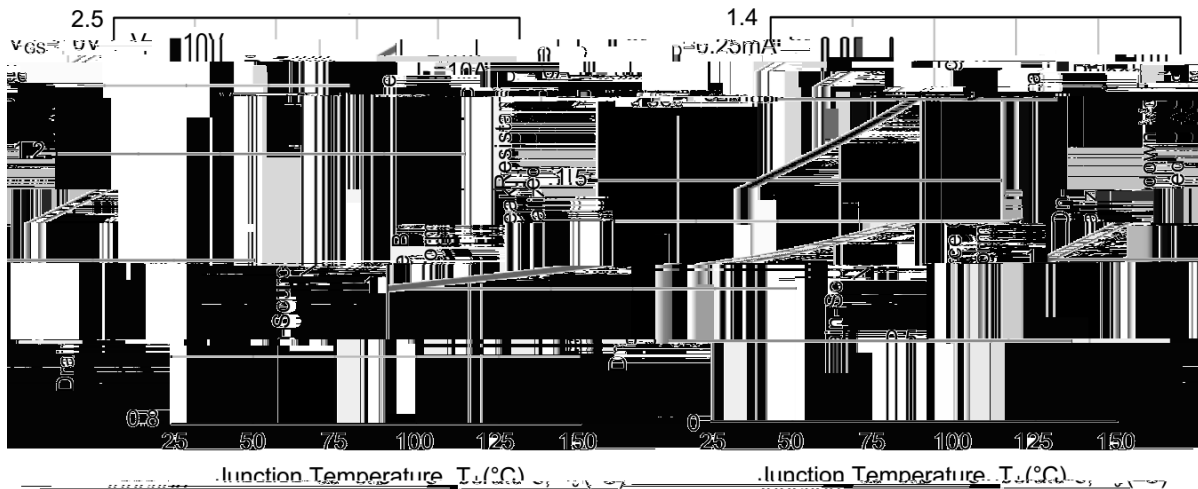
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	650	V
Drain Current	$I_D(T_c=25^{\circ}C)$	20	A
Drain Current - Pulsed	I_{DM}	40	A
Gate-Source Voltage	V_{GS}	± 30	V

0e,799340J Single Pulsed Avalanche Energy 7.0282-73(R/TTEAS 1 4810(E)TJ7.0392TTTc0 0

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	08SbE	08SbE
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/ Electrical Characteristic Curve



2. Breakdown Voltage vs. Junction Temperature

1. Drain-Source On-Resistance vs. Junction Temperature

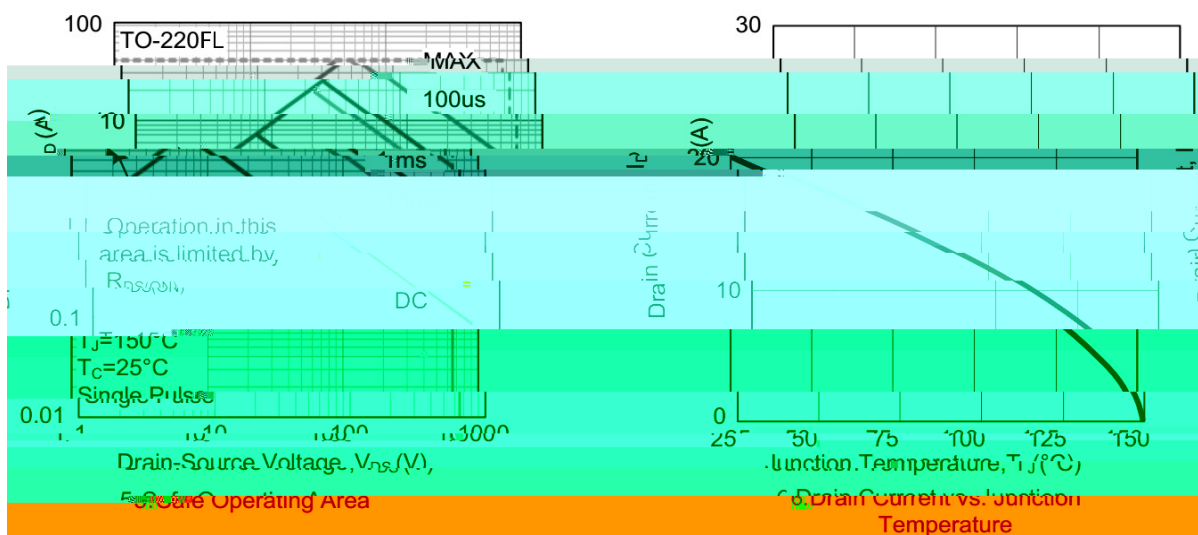
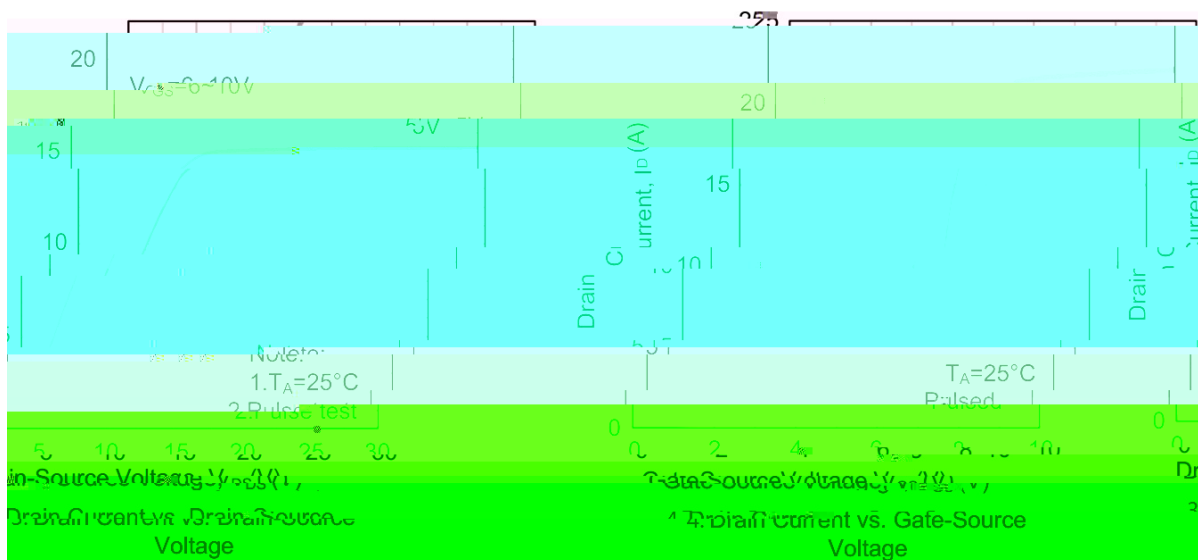
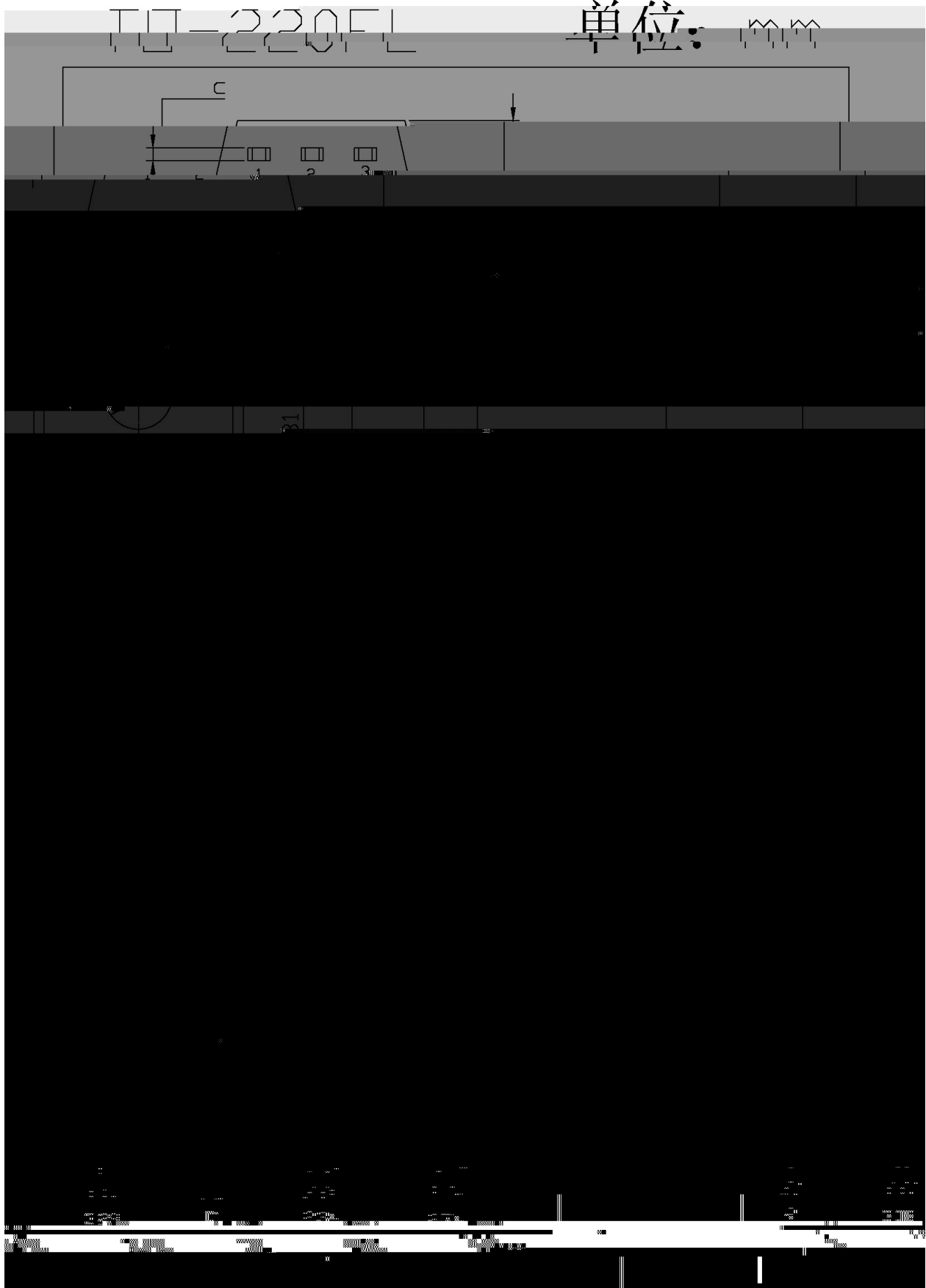


Figure Operating Area

3. Drain Current vs. Junction Temperature

/ Package Dimensions



BRFL20N65


() / Temperature Profile for Dip Soldering(Pb-Free)

Note:

- | | | | |
|---|-----------|--------------|---|
| 1 | 25 150 | 60 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. |
| 3 | 2 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec
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/ Packaging SPEC.

/ TUBE